

# N-channel 30 V 13.6 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 24 October 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

### 1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	32	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	26	W
Tj	junction temperature		-55	-	175	°C
Static charac	cteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	14.4	16.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	11.6	13.6	mΩ
Dynamic cha	aracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.2	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$ see Figure 14; see Figure 15	-	4	-	nC



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S S

SOT669 (LFPAK; Power-SO8)

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PSMN013-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	32	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	23	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4	-	130	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	26	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
$V_{ESD}$	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	130	-	V
Source-drai	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	23	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$	-	130	Α
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 32 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped; see Figure 3	-	7	mJ

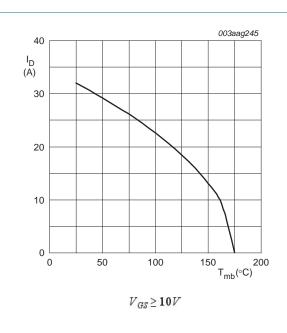


Fig 1. Continuous drain current as a function of mounting base temperature

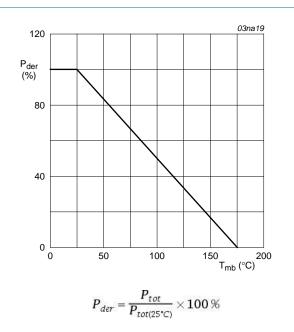
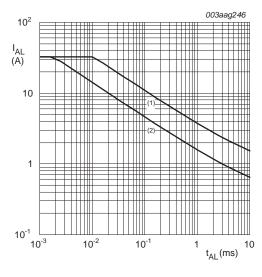


Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1)  $T_{j\ (int)} = 25^{\circ}C;$  (2)  $T_{j\ (int)} = 100^{\circ}C$ 

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

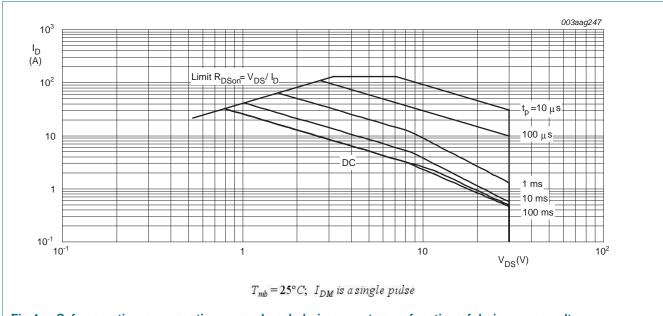
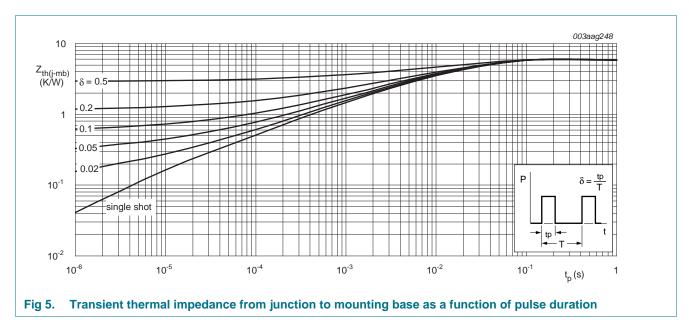


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	5.66	5.83	K/W



### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
•	racteristics	Conditions	.,,,,,,	1 y P	Max	Oilit
	drain-source breakdown	$I_D = 250 \mu\text{A};  V_{GS} = 0  V;  T_i = 25 ^{\circ}\text{C}$	30	_	-	V
V <sub>(BR)DSS</sub>	voltage	$I_D = 250 \mu\text{A};  V_{GS} = 0 \text{V};  I_j = 25 \text{°C}$ $I_D = 250 \mu\text{A};  V_{GS} = 0 \text{V};  T_i = -55 \text{°C}$		-	-	V
.,			27		-	
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see Figure 10; see Figure 11	1.05	1.68	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	14.4	16.9	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	27.2	mΩ
	$V_{GS} = 10 \text{ V; } I_D = 10 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 12	-	11.6	13.6	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	22.1	mΩ
$R_G$	gate resistance	f = 1 MHz	-	2.12	4.24	Ω
Dynamic (	characteristics					
Q <sub>G(tot)</sub>		$I_D = 10 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	8.3	-	nC
		I <sub>D</sub> = 10 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; see Figure 14; see Figure 15	-	4	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	7.7	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 10 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;	-	1.3	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	0.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	0.4	-	nC
$Q_{GD}$	gate-drain charge		-	1.2	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 15 V; see <u>Figure 14</u> ; see Figure 15	-	2.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	521	-	рF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}$ ; see Figure 16		128	-	рF
C <sub>rss</sub>	reverse transfer capacitance	<del>-</del>	<u> </u>	39	_	рF
	rovoroo manoror oapaonarios					•
	turn-on delay time	V <sub>20</sub> - 15 V: R <sub>1</sub> - 0.6 O: V <sub>20</sub> - 4.5 V:	-	11 6	-	
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_{L}$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V; $R_{G(ext)}$ = 4.7 $\Omega$	-	11.6 a a	-	ns
$t_{d(on)}$ $t_r$ $t_{d(off)}$	turn-on delay time rise time turn-off delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V; $R_{G(ext)}$ = 4.7 $\Omega$	-	9.9 16.3	-	ns ns

### N-channel 30 V 13.6 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; $ $T_j = 25 \text{ °C}$	-	3.3	-	nC
Source-drain diode						
V <sub>SD</sub>	source-drain voltage	$I_S = 10 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.86	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	16	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	6	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 10 \text{ A};$	-	9.5	-	ns
t <sub>b</sub>	reverse recovery fall time	$dI_S/dt = -100 A/\mu s; V_{DS} = 15 V;$ see Figure 18	-	6.5	-	ns

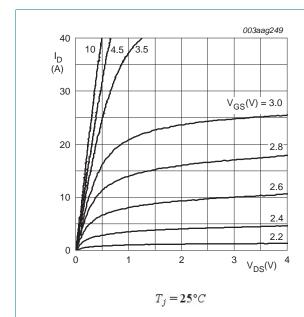


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

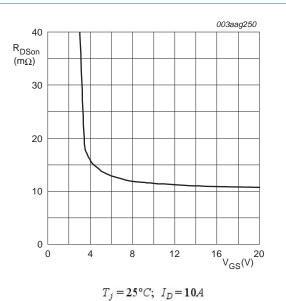


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

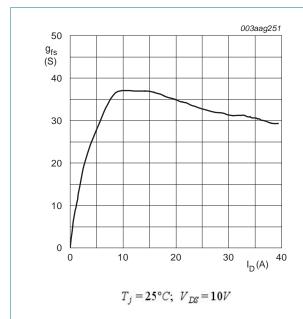


Fig 8. Forward transconductance as a function of drain current; typical values

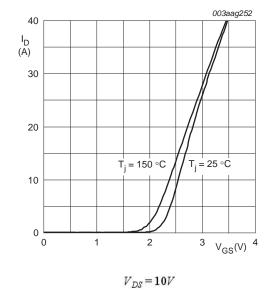


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

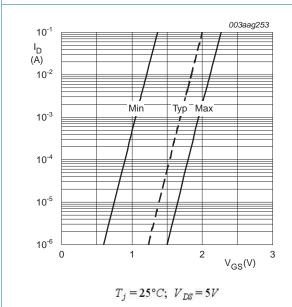


Fig 10. Sub-threshold drain current as a function of gate-source voltage

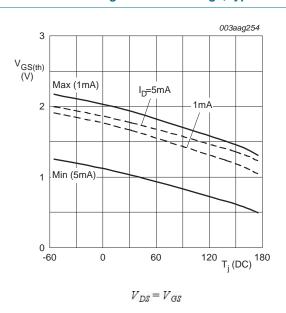


Fig 11. Gate-source threshold voltage as a function of junction temperature

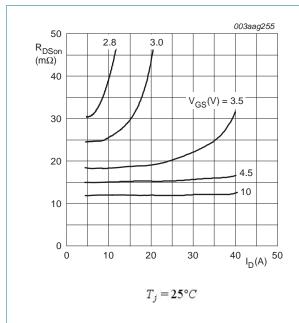


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

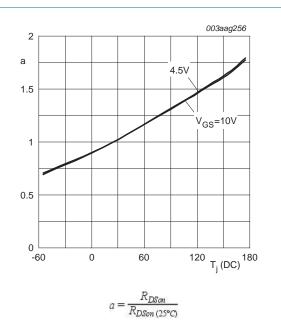


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

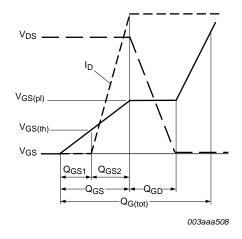


Fig 14. Gate charge waveform definitions

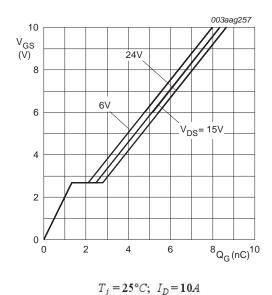


Fig 15. Gate-source voltage as a function of gate charge; typical values

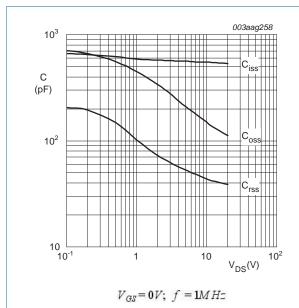


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

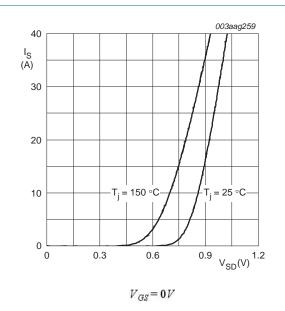


Fig 17. Source current as a function of source-drain voltage; typical values

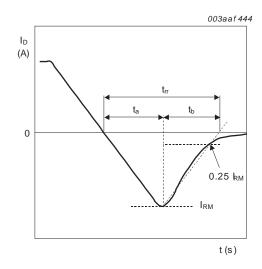


Fig 18. Reverse recovery timing definition

### 7. Package outline



**SOT669** 

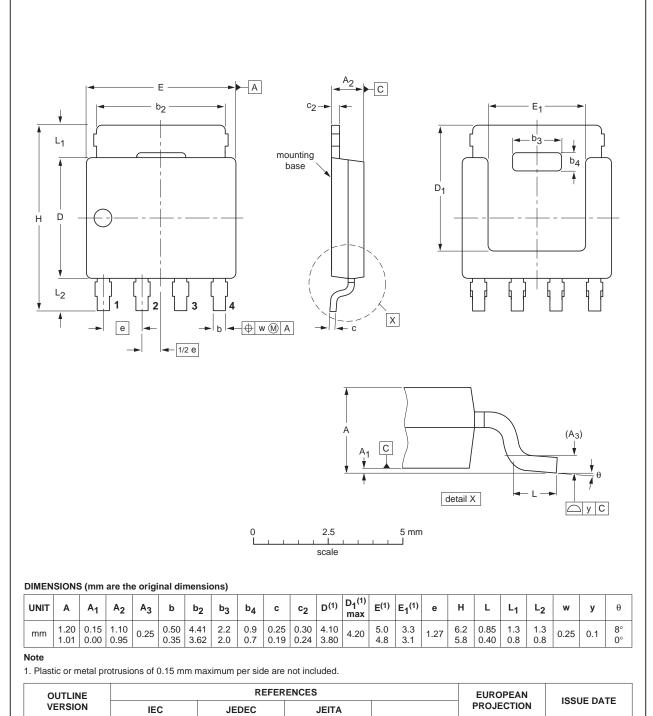


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

MO-235

PSMN013-30YLC

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SOT669

N-channel 30 V 13.6 mΩ logic level MOSFET in LFPAK using NextPower technology

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-30YLC v.3	20111024	Product data sheet	-	PSMN013-30YLC v.2
Modifications:	<ul> <li>Status changed from</li> </ul>	om preliminary to product.		
	<ul> <li>Various changes to</li> </ul>	o content.		
PSMN013-30YLC v.2	20110929	Preliminary data sheet	-	PSMN013-30YLC v.1

#### N-channel 30 V 13.6 mΩ logic level MOSFET in LFPAK using NextPower technology

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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# **PSMN013-30YLC**

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